

1. Scope :

1-1. This specification applies to N channel silicon MOSFET chips,
Device no. PM-0122

2. Structure :

- 2-1. Planar type.
- 2-2. Electrodes.
Source : Aluminum alloy .
Gate : Aluminum alloy .
Drain : Ti/Au.

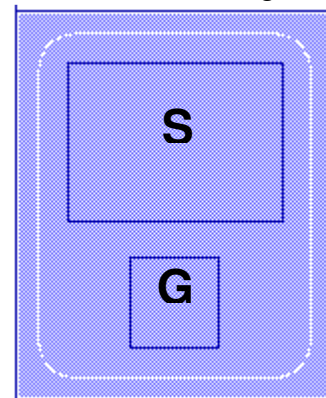
3. Size :

- 3-1. Chip size : 16.5 mils × 20.1 mils (0.420 mm × 0.510 mm).
- 3-2. Chip thickness : 9 ± 1.0 mils (0.229 ± 0.025 mm).
- 3-3. Pad size :
Source : 10.5 mils × 7.8 mils (0.267 mm × 0.198 mm).
Gate : 4.3 mils × 4.4 mils (0.109 mm × 0.112 mm).
- 3-4. Pattern drawing : Refer to the attached drawing.

4. Absolute maximum rating (Ta = 25 °C)

Parameter	Symbol	Rating	Unit
Continuous drain current V _{GS} =10V	I _{D(m)}	0.5	A
Drain-source Voltage	V _{DSS}	60	V
Gate-source Voltage	V _{GS}	±20	V
Operating junction and storage temperature range	T _J T _{STG}	-40to+150	°C

Pattern drawing



5. Electrical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain to source breakdown voltage	BV _{DSS}	V _{GS} = 0V I _D = 100uA	60			V
Gate threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} I _D = 1mA	1.0		2.5	V
Gate to source leakage current	I _{GSS}	V _{GS} = ±20V V _{DS} = 0V			± 100	nA
Drain to source leakage current	I _{DSS}	V _{GS} = 0V V _{DS} = 60V			1	μA
Drain to source on resistance	R _{DS1(on)}	V _{GS} = 5V I _D = 50mA			5	Ω
	R _{DS2(on)}	V _{GS} = 10V I _D = 500mA			4.5	Ω
Diode forward voltage drop	V _{SD}	V _{GS} = 0V I _{SD} = 100mA		0.84	1.5	V

